

2SK2577(Tentative)

Silicon N-Channel Power F-MOS

■ Features

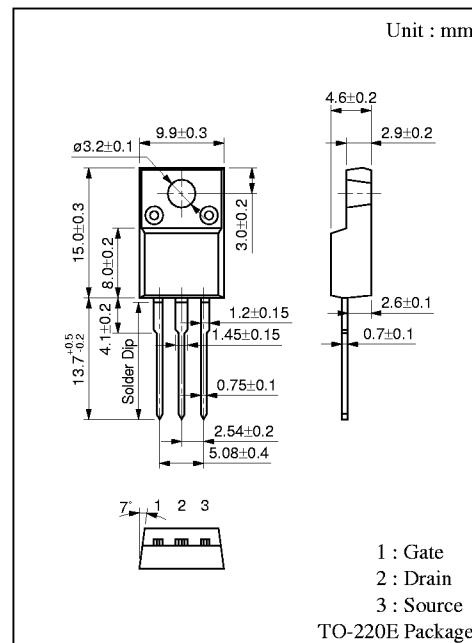
- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

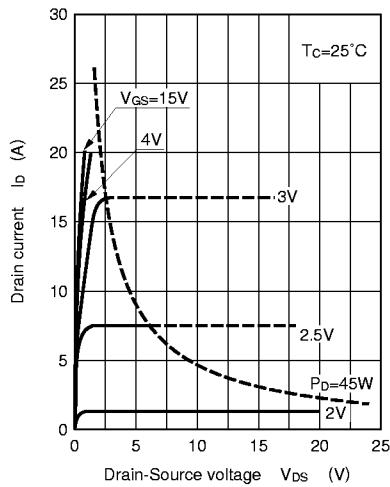
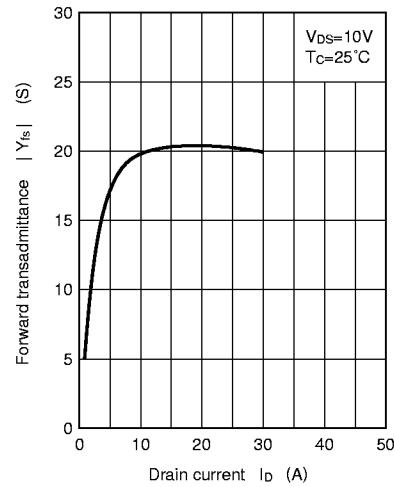
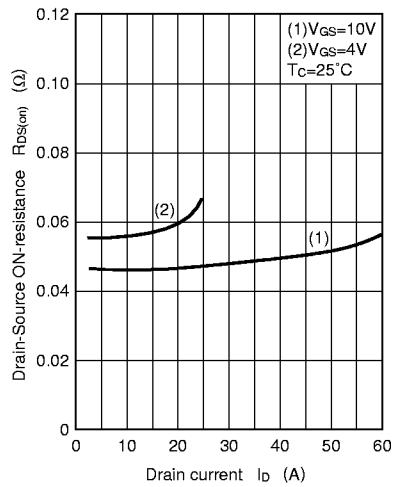
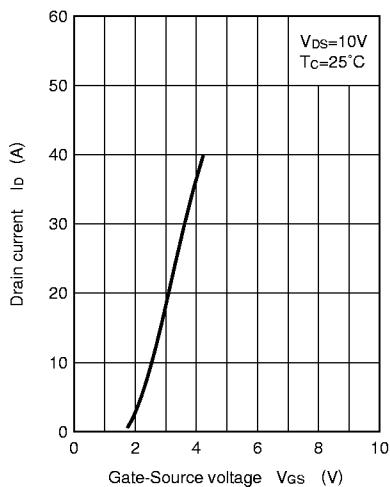
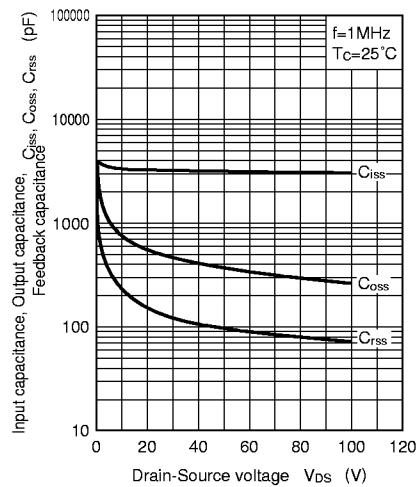
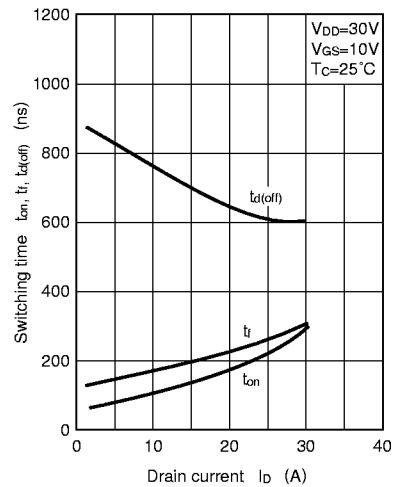
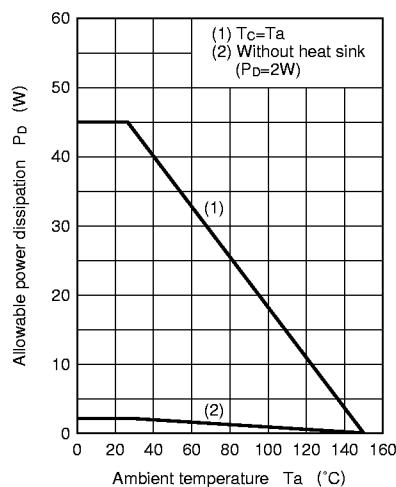
■ Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	V_{DSS}	100	V
Gate-Source voltage	V_{GSS}	± 20	V
Drain current	DC	I_D	A
	Pulse	I_{DP}	A
Avalanche energy capability	EAS *	20	mJ
Allowable power dissipation	$T_c = 25^\circ\text{C}$	P_D	W
	Ta = 25°C	45	
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

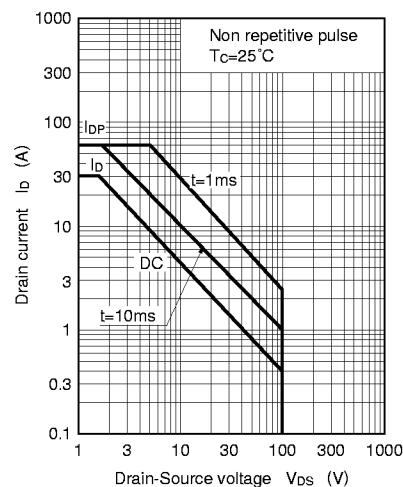
* $L = 0.1\text{mH}$, $I_L = 20\text{A}$, 1 pulse

■ Electrical Characteristics ($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	$V_{DS} = 80\text{V}$, $V_{GS} = 0$			10	μA
Gate-Source leakage current	I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0$			± 1	μA
Drain-Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}$, $V_{GS} = 0$	100			V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	1		2.5	V
Drain-Source ON-resistance	$R_{DS(on)1}$	$V_{GS} = 10\text{V}$, $I_D = 15\text{A}$		48	70	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS} = 4\text{V}$, $I_D = 10\text{A}$		56	85	$\text{m}\Omega$
Forward transadmittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$, $I_D = 15\text{A}$	12	20		S
Diode forward voltage	V_{DSF}	$I_{DR} = 30\text{A}$, $V_{GS} = 0$			-1.7	V
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		3350		pF
Output capacitance	C_{oss}			800		pF
Feedback capacitance	C_{rss}			230		pF
Turn-on time	t_{on}	$V_{DD} = 30\text{V}$, $I_D = 15\text{A}$ $V_{GS} = 10\text{V}$, $R_L = 2\Omega$		130		ns
Fall time	t_f			190		ns
Turn-off time (delay time)	$t_{d(off)}$			700		ns
Channel-Case heat resistance	$R_{th(ch-c)}$				2.78	°C/W
Channel-Atmosphere heat resistance	$R_{th(ch-a)}$				62.5	°C/W

$I_D - V_{DS}$  $|Y_{fs}| - I_D$  $R_{DS(on)} - I_D$  $I_D - V_{GS}$  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$  $t_{on}, t_r, t_f, t_{d(off)} - I_D$  $P_D - T_a$ 

Area of safe operation (ASO)

 $R_{DS(on)} - I_D$ 